

Notice of References Cited	Application/Control No. 10/788,411	Applicant(s)/Patent Under Reexamination HIRUKAWA ET AL.	
	Examiner <i>J-1/25/06</i> James A. Menefee	Art Unit 2828	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	C	US-6,195,373 B1	02-2001	Fukunaga, Toshiaki	372/45.01
*	D	US-6,127,691 A	10-2000	Fukunaga et al.	257/17
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	T. Fukunaga et al., "Highly Reliable Operation of High-Power InGaAsP/InGaP/AlGaAs 0.8 um Separate Confinement Heterostructure Lasers," Jpn. J. Appl. Phys., vol. 34, no. 9B, Sept. 15, 1995, pp. L1175-L1177.
	V	J.K. Wade et al., "6.1 W COntinuous Wave Front-Facet Power From Al-Free Active-Region (lambda=805 nm) Diode Lasers," Appl. Phys. Lett., vol. 72, no. 1, Jan. 5, 1998, pp. 4-6.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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